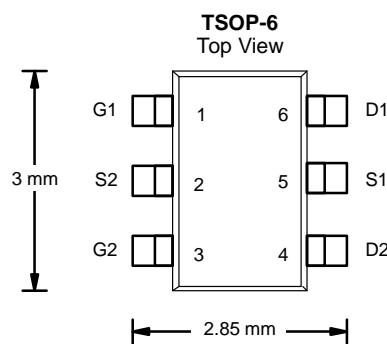


Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 20	0.075 at $V_{GS} = - 4.5V$	- 4.0	2.7 nC
	0.100 at $V_{GS} = - 2.5 V$	- 3.2	

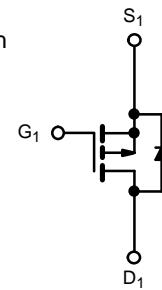
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

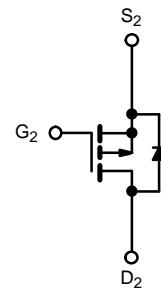


APPLICATIONS

- Load Switch for Portable Applications
- Battery Switch for Portable Devices
- Computers
 - Bus Switch
 - Load Switch



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ C$)	I_D	- 4.0	A
		- 3.3	
		- 3.6 ^{b, c}	
		- 3.1 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 12	
Continuous Source-Drain Diode Current	I_S	- 1.17	
		- 0.95 ^{b, c}	
Maximum Power Dissipation	P_D	1.4	W
		0.9	
		1.14 ^{b, c}	
		0.73 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	93	110	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	75	

Notes:

- $T_C = 25^\circ C$.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 150 °C/W.

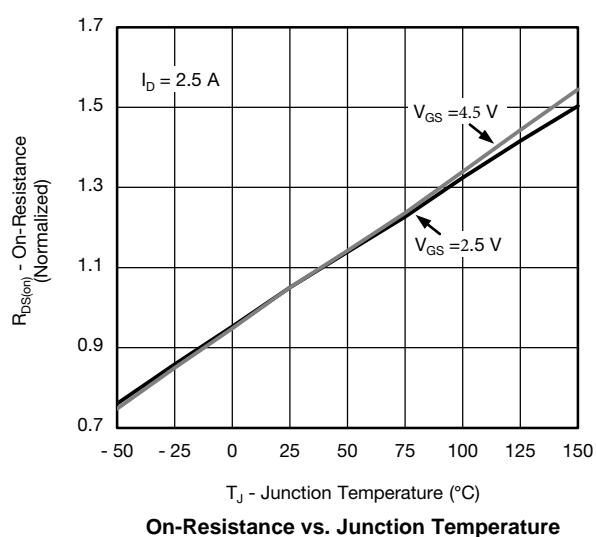
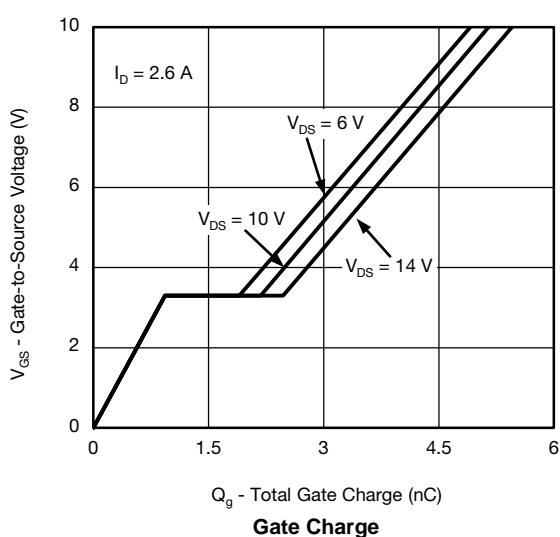
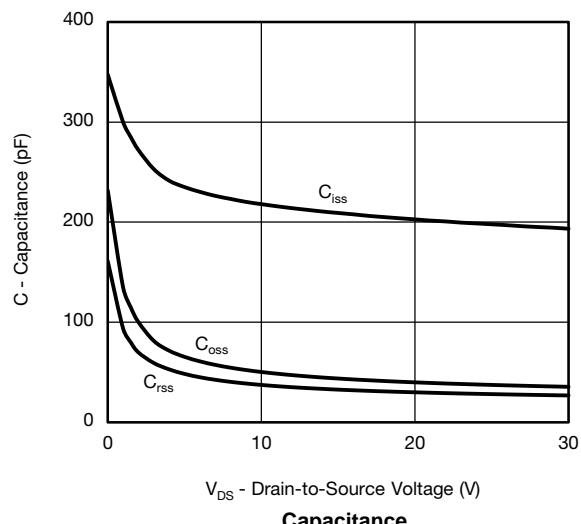
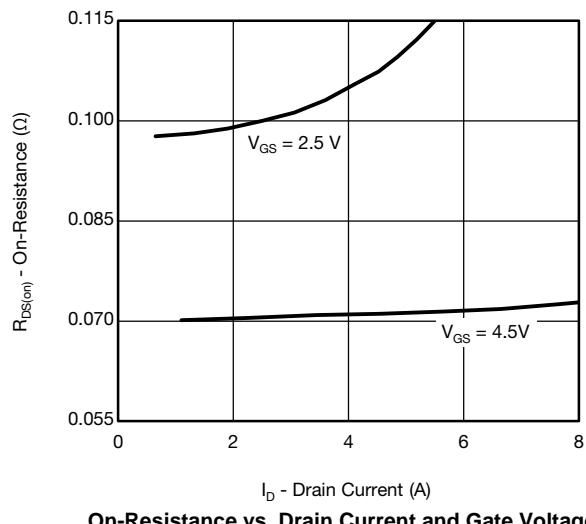
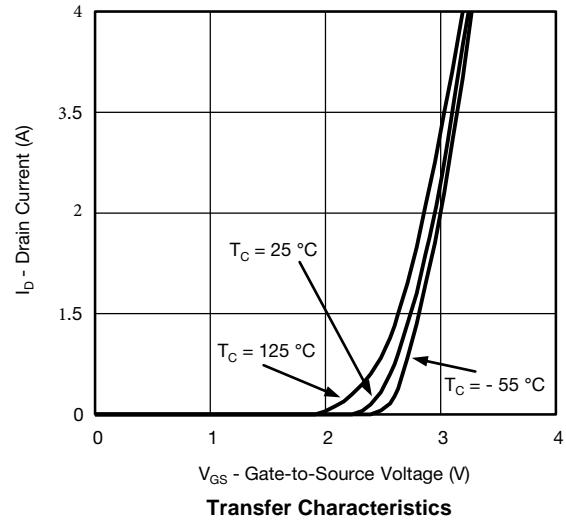
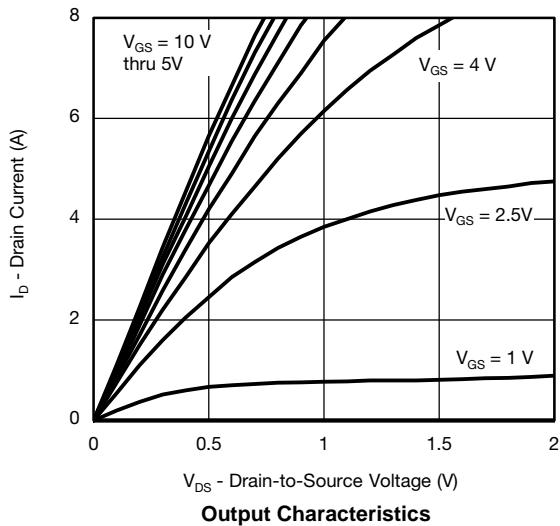
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

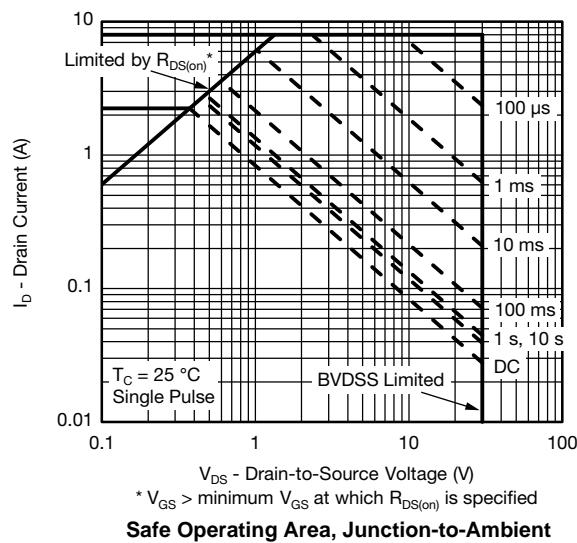
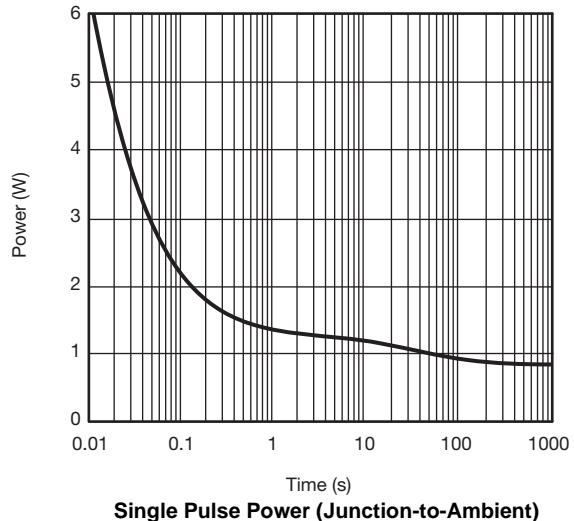
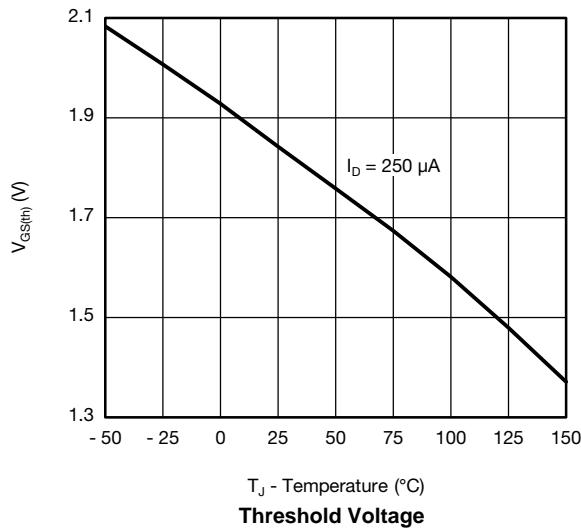
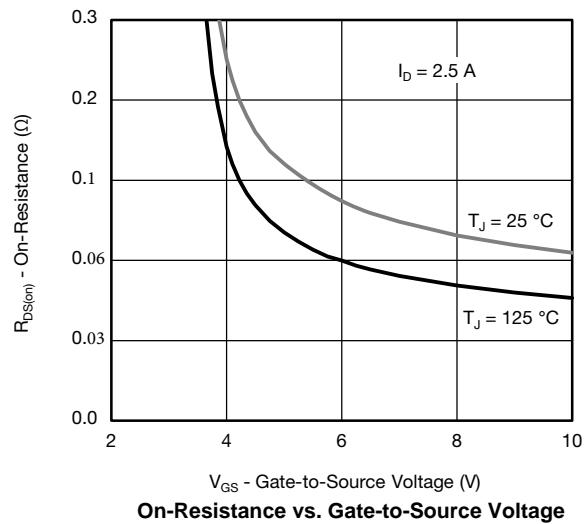
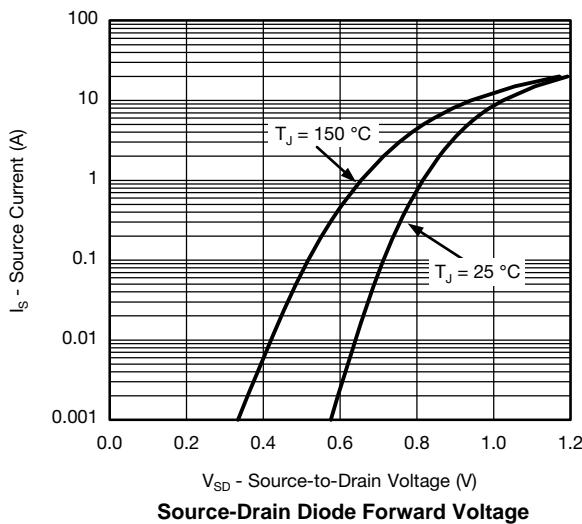
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-17		$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			3.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-0.5		-2.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20 \text{ V}$, $V_{GS} = 0 \text{ V}$		1		μA
		$V_{DS} = -20 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \leq -5 \text{ V}$, $V_{GS} = -4.5 \text{ V}$	-8			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -4.5 \text{ V}$, $I_D = -2.5 \text{ A}$		0.075		Ω
		$V_{GS} = -2.5 \text{ V}$, $I_D = -1 \text{ A}$		0.100		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10 \text{ V}$, $I_D = -2.6 \text{ A}$		5		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		210		pF
Output Capacitance	C_{oss}			45		
Reverse Transfer Capacitance	C_{rss}			33		
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -2.6 \text{ A}$		5.2	8	nC
				2.7	4	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -2.6 \text{ A}$		0.94		
Gate-Drain Charge	Q_{gd}			1.3		
Gate Resistance	R_g	$f = 1 \text{ MHz}$	2	7	14	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -10 \text{ V}$, $R_L = 7.1 \Omega$ $I_D \equiv -2.1 \text{ A}$, $V_{GEN} = -4.5 \text{ V}$, $R_g = 1 \Omega$		39	59	ns
Rise Time	t_r			25	38	
Turn-Off Delay Time	$t_{d(\text{off})}$			13	20	
Fall Time	t_f			9	18	
Turn-On Delay Time	$t_{d(\text{on})}$			5	10	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(\text{off})}$			14	21	
Fall Time	t_f			7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			1.17	A
Pulse Diode Forward Current	I_{SM}				8	
Body Diode Voltage	V_{SD}	$I_S = -2.1 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2.1 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		13	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}			6	12	
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			4		

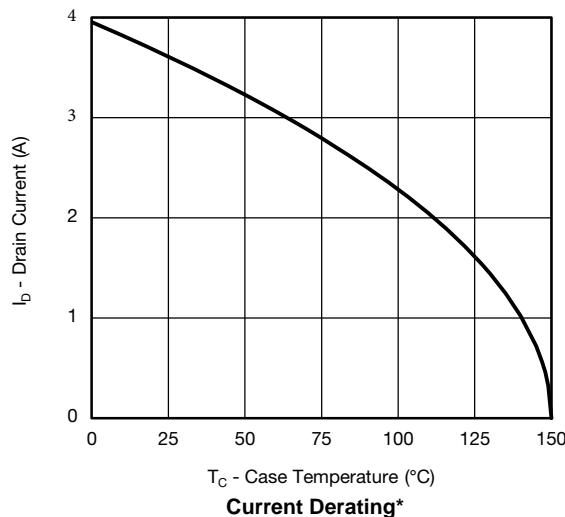
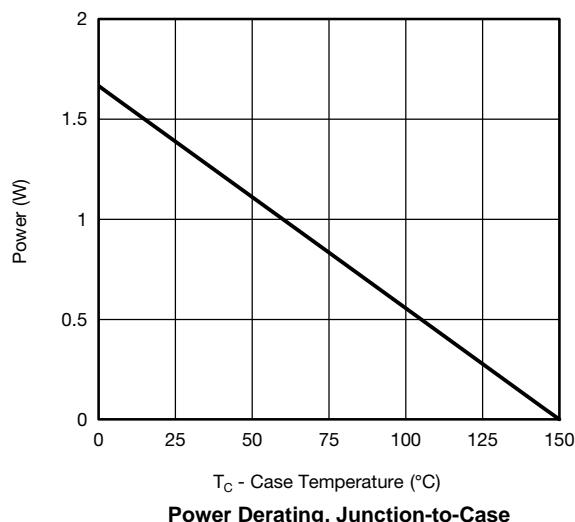
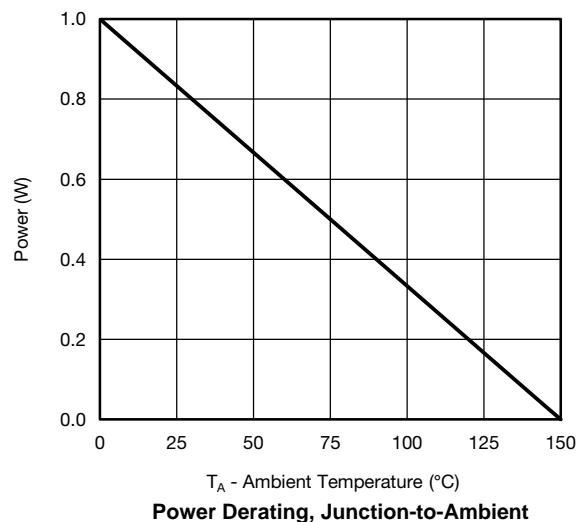
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

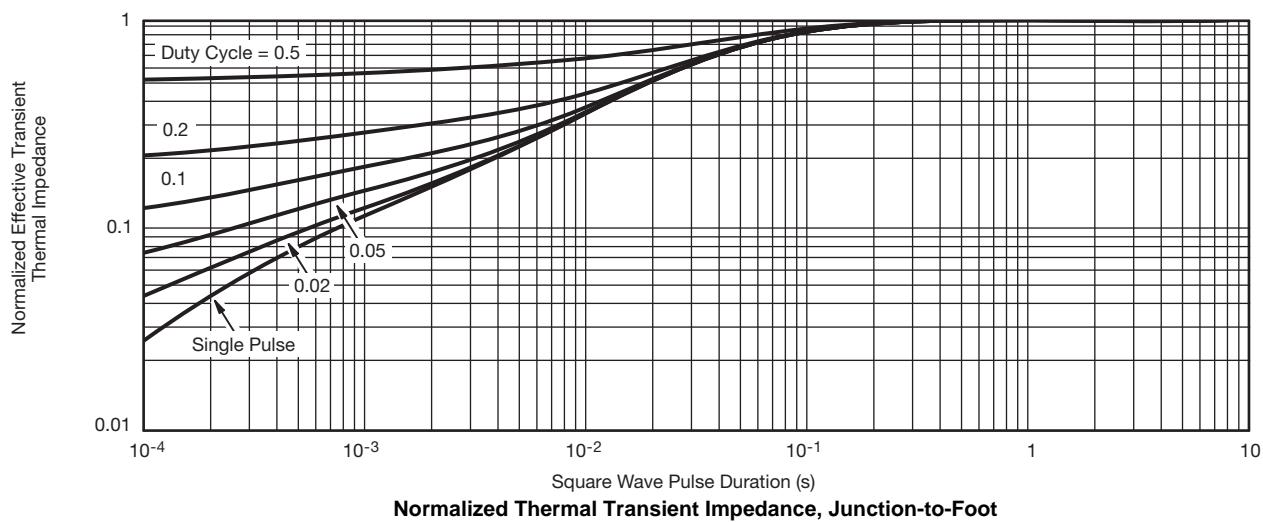
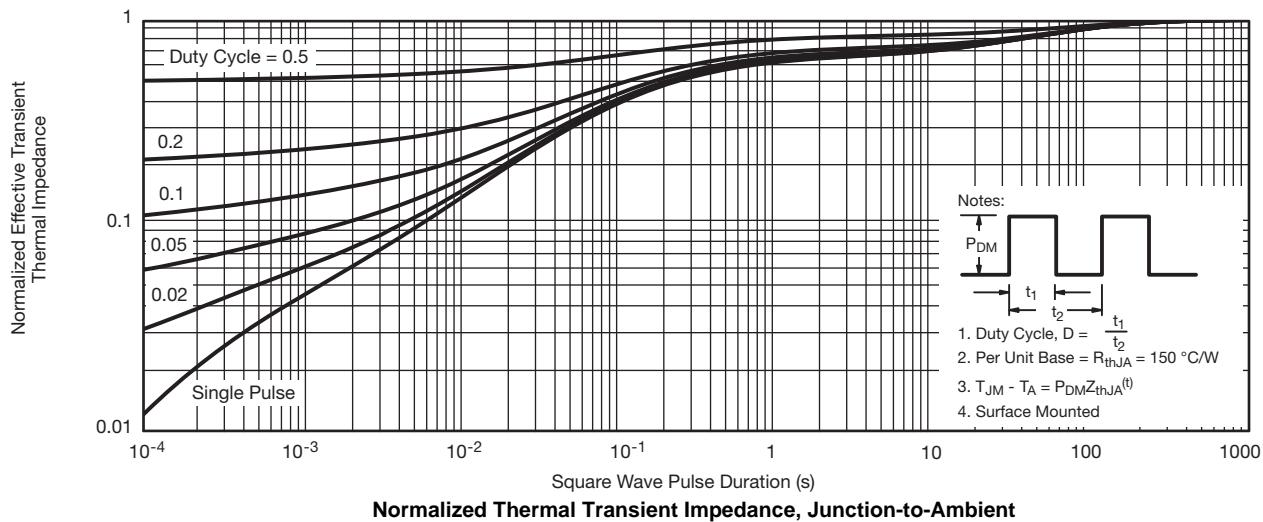
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power Derating, Junction-to-Case

Power Derating, Junction-to-Ambient

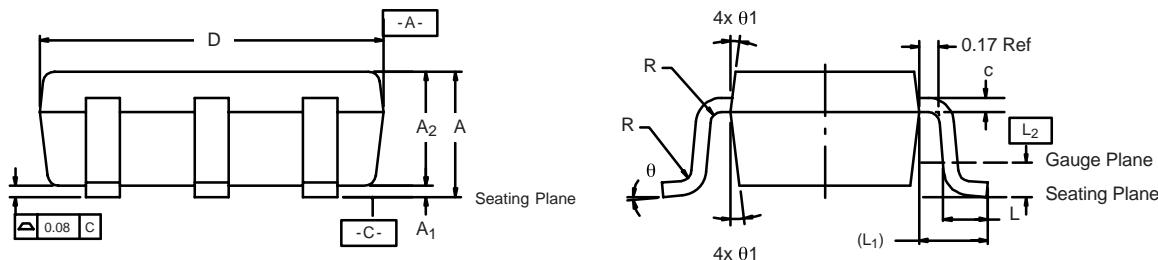
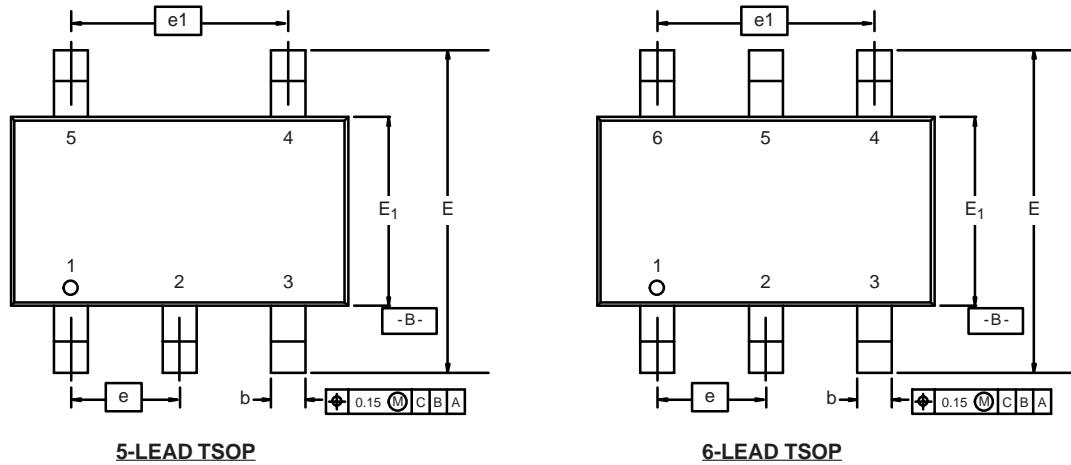
* The power dissipation P_D is based on $T_{J(\text{max})} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

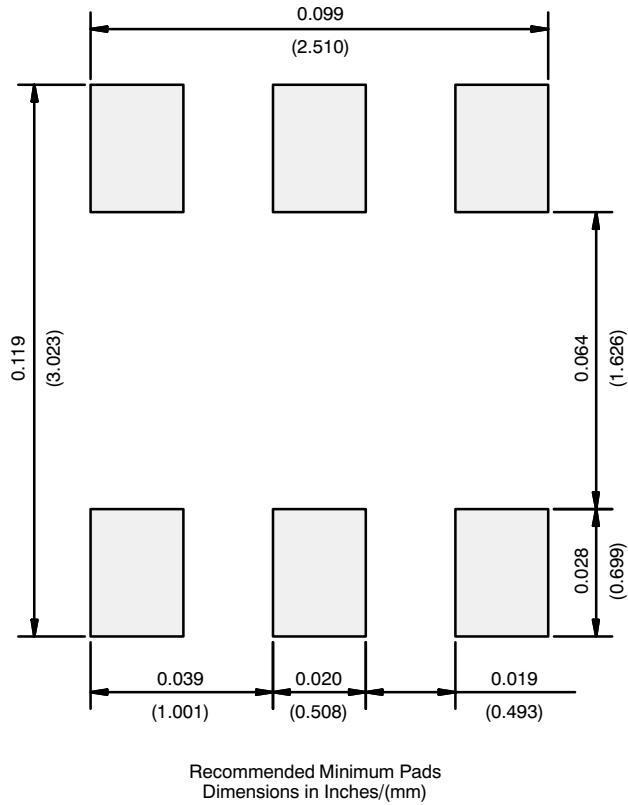


TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A₁	0.01	-	0.10	0.0004	-	0.004
A₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L₁	0.60 Ref			0.024 Ref		
L₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ₁	7° Nom			7° Nom		

RECOMMENDED MINIMUM PADS FOR TSOP-6

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